

# **BUK78150-55A**

# N-channel TrenchMOS standard level FET Rev. 02 — 16 June 2010

**Product data sheet** 

### **Product profile**

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

Suitable for standard level gate drive sources

#### 1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$	-	-	55	V
drain current	$V_{GS} = 10 \text{ V}; T_{sp} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	5.5	Α
total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	8	W
acteristics					
drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	278	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	128	150	mΩ
ruggedness					
non-repetitive drain-source avalanche energy	$I_D = 5 \text{ A}; V_{sup} \le 55 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 ^{\circ}C; \text{ unclamped}$	-	-	25	mJ
	drain-source voltage drain current  total power dissipation acteristics drain-source on-state resistance  ruggedness non-repetitive drain-source	drain-source voltage $ T_{j} \geq 25 \text{ °C}; T_{j} \leq 150 \text{ °C} $ $ voltage $ $ drain current                                   $	$\begin{array}{lll} \text{drain-source} & T_{j} \geq 25 \text{ °C}; \ T_{j} \leq 150 \text{ °C} & - \\ \text{voltage} & & & & & & & \\ \text{drain current} & V_{GS} = 10 \text{ V}; \ T_{sp} = 25 \text{ °C}; & - \\ \text{see Figure 1}; \ \text{see Figure 3} & & & & \\ \text{total power} & T_{sp} = 25 \text{ °C}; \ \text{see Figure 2} & - \\ \text{dissipation} & & & & & \\ \text{acteristics} & & & & & \\ \text{drain-source} & V_{GS} = 10 \text{ V}; \ I_{D} = 5 \text{ A}; & - \\ T_{j} = 150 \text{ °C}; & & & & \\ \text{resistance} & & & & & \\ \text{see Figure 12}; \ \text{see Figure 13} & & & \\ \hline V_{GS} = 10 \text{ V}; \ I_{D} = 5 \text{ A}; & - \\ T_{j} = 25 \text{ °C}; & & & & \\ \text{see Figure 12}; \ \text{see Figure 13} & & & \\ \hline \text{ruggedness} & & & & \\ \text{non-repetitive} & I_{D} = 5 \text{ A}; \ V_{sup} \leq 55 \text{ V}; & - \\ \text{R}_{GS} = 50  \Omega; \ V_{GS} = 10 \text{ V}; & & \\ \hline \end{array}$	drain-source voltage $T_{j} \geq 25 \text{ °C; } T_{j} \leq 150 \text{ °C} \qquad - \qquad -$ where $V_{GS} = 10 \text{ V; } T_{sp} = 25 \text{ °C; } \qquad - \qquad -$ see $Figure 1; \text{ see } Figure 3$ total power dissipation $T_{sp} = 25 \text{ °C; see } Figure 2 \qquad - \qquad -$ where $T_{sp} = 25 \text{ °C; see } Figure 2 \qquad - \qquad -$ where $T_{j} = 150 \text{ °C; } \qquad -$ resistance $T_{j} = 150 \text{ °C; } \qquad -$ resistance $See \qquad Figure 12; \text{ see } Figure 13$ $V_{GS} = 10 \text{ V; } I_{D} = 5 \text{ A; } \qquad - \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ see $Figure 12; \text{ see } Figure 13$ ruggedness $T_{j} = 25 \text{ °C; } \qquad -$ see $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 128 $T_{j} = 25 \text{ °C; } \qquad -$ 129 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } \qquad -$ 120 $T_{j} = 25 \text{ °C; } $	drain-source voltage $T_{j} \geq 25 \text{ °C}; T_{j} \leq 150 \text{ °C} \qquad - \qquad 55$ drain current $V_{GS} = 10 \text{ V}; T_{sp} = 25 \text{ °C}; \qquad - \qquad 5.5$ see Figure 1; see Figure 3 $T_{sp} = 25 \text{ °C}; \text{ see Figure 2} \qquad - \qquad 8$ dissipation $T_{sp} = 25 \text{ °C}; \text{ see Figure 2} \qquad - \qquad 8$ drain-source on-state $T_{j} = 150 \text{ °C}; \qquad - \qquad 278$ on-state $T_{j} = 150 \text{ °C}; \qquad \text{see Figure 13}$ $V_{GS} = 10 \text{ V}; I_{D} = 5 \text{ A}; \qquad - \qquad 128 \text{ 150}$ $V_{GS} = 10 \text{ V}; I_{D} = 5 \text{ A}; \qquad - \qquad 128 \text{ 150}$ $T_{j} = 25 \text{ °C}; \qquad \text{see Figure 12}; \text{ see Figure 13}$ ruggedness $T_{j} = 25 \text{ °C}; \qquad \text{see Figure 13}$ ruggedness $T_{j} = 5 \text{ A}; \qquad - \qquad 25 \text{ drain-source}$ $T_{j} = 5 \text{ A}; \qquad - \qquad 25 \text{ drain-source}$ $T_{j} = 5 \text{ A}; \qquad - \qquad 25 \text{ drain-source}$



# 2. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	4	D
3	S	source		
4	D	drain	□ <sub>1</sub> □ <sub>2</sub> □ <sub>3</sub> SOT223 (SC-73)	mbb076 S

# 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK78150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	-	55	V
V <sub>GS</sub>	gate-source voltage		-20	-	20	V
$I_D$	drain current	$T_{sp}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	5.5	Α
		$T_{sp}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	3.8	Α
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; $t_p$ ≤ 10 μs; pulsed; see Figure 3	-	-	22	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	8	W
T <sub>stg</sub>	storage temperature		-55	-	150	°C
T <sub>j</sub>	junction temperature		-55	-	150	°C
Source-drai	in diode					
Is	source current	T <sub>sp</sub> = 25 °C	-	-	5.5	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{sp} = 25 \ ^{\circ}C$	-	-	22	Α
Avalanche i	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 5 A; $V_{sup} \le$ 55 V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	25	mJ

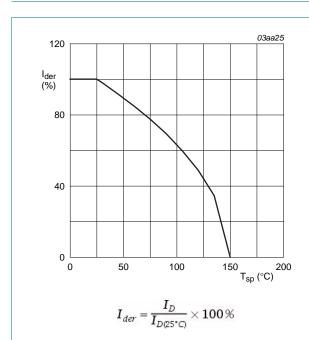
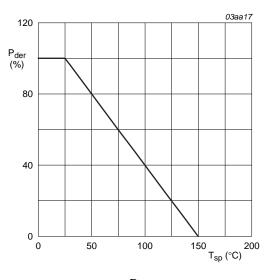
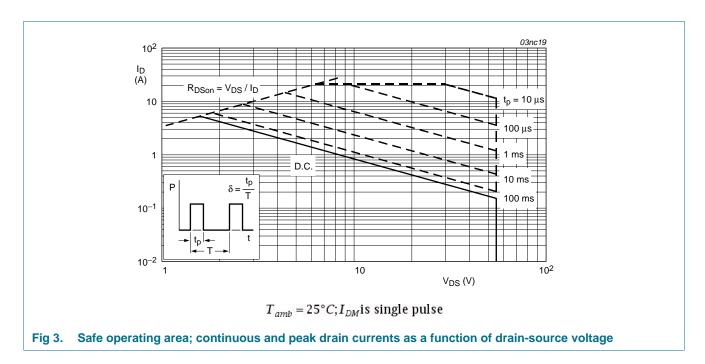


Fig 1. Normalized continuous drain current as a function of solder point temperature



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$ 

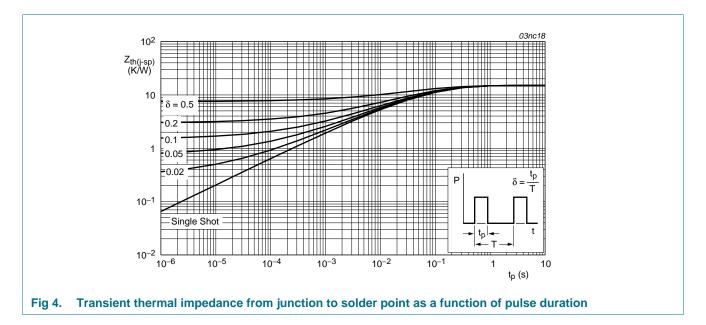
Fig 2. Normalized total power dissipation as a function of solder point temperature



#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	see Figure 4	-	70	-	K/W



## 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	V <sub>(BR)DSS</sub> drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 11	2	3	4	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see Figure 11	1	-	-	V	
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$ ; $I_D = 5 \text{ A}$ ; $T_j = 150 \text{ °C}$ ; see Figure 12; see Figure 13	-	-	278	mΩ
		$V_{GS} = 10 \text{ V}$ ; $I_D = 5 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 12; see Figure 13	-	128	150	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	170	230	pF
C <sub>oss</sub>	output capacitance	$T_j = 25$ °C; see <u>Figure 14</u>	-	54	65	рF
C <sub>rss</sub>	reverse transfer capacitance		-	37	52	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	8	-	ns
t <sub>f</sub>	fall time		-	10	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	32	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	50	-	nC

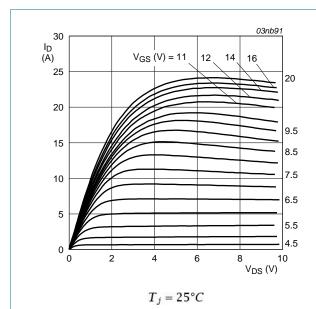


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

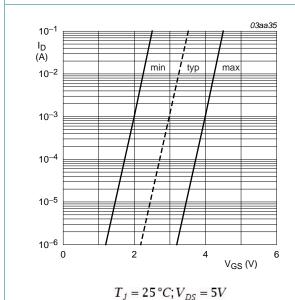


Fig 7. Sub-threshold drain current as a function of gate-source voltage

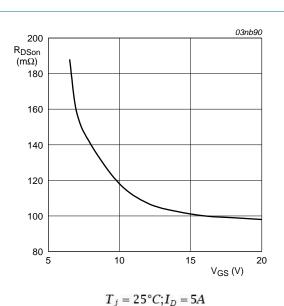


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

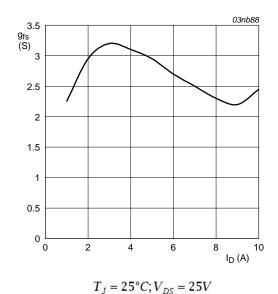
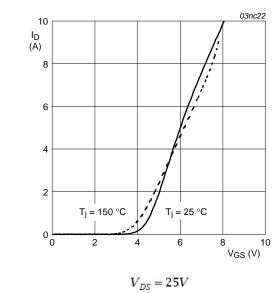
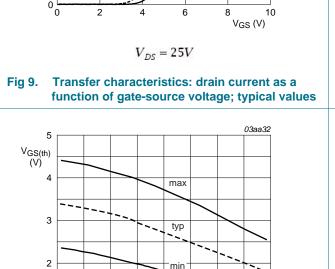


Fig 8. Forward transconductance as a function of drain current; typical values





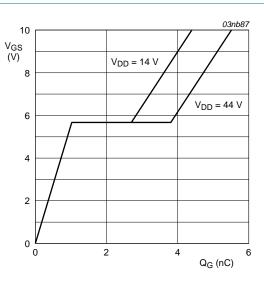
 $I_D = 1mA; V_{DS} = V_{GS}$ 

60

180

T<sub>j</sub> (°C)

Fig 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25^{\circ}C; I_D = 5A$ 

Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

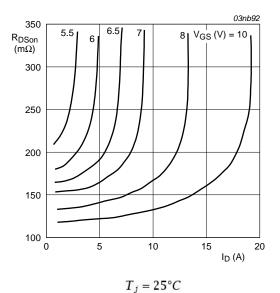


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

-60

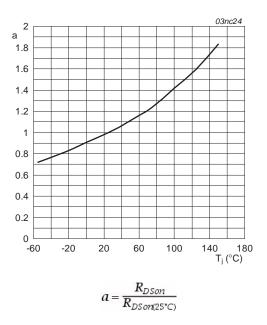
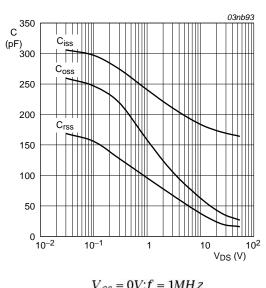


Fig 13. Normalized drain source on-state resistance factor as a function of junction temperature



 $V_{GS} = 0V; f = 1MHz$ 

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

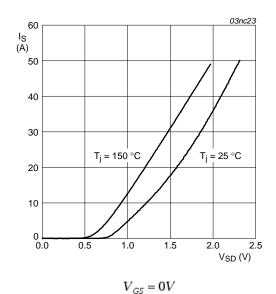


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

### 7. Package outline

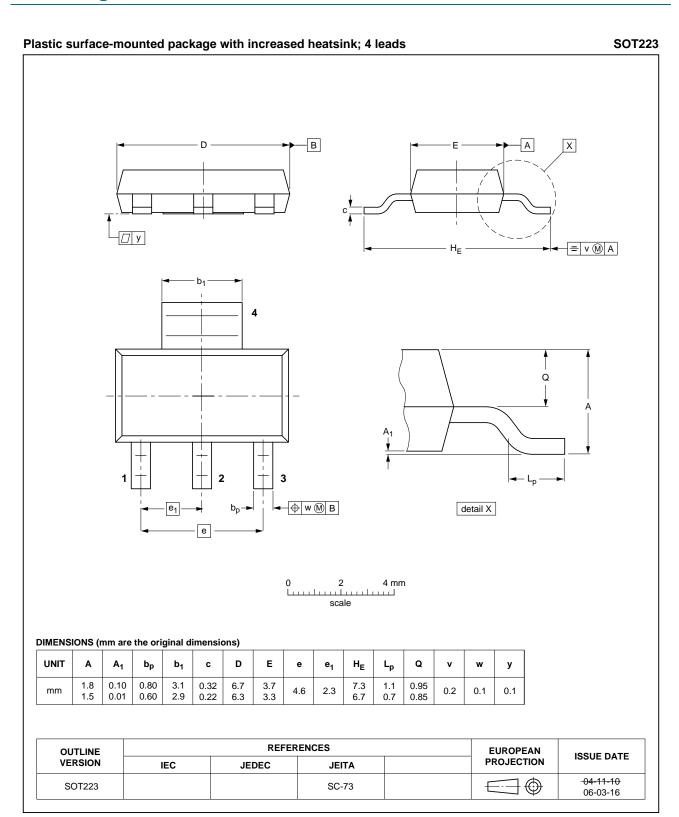


Fig 16. Package outline SOT223 (SC-73)

BUK78150-55A

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK78150-55A v.2	20100616	Product data sheet	-	BUK78150-55A v.1
Modifications:		nat of this data sheet has been redesigned to comply with the new identity guidelin Semiconductors		
	<ul> <li>Legal texts</li> </ul>	have been adapted to the i	new company name where	appropriate.
BUK78150-55A v.1 (9397 750 07738)	20010130	Product Specification	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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# BUK78150-55A

### **Nexperia**

N-channel TrenchMOS standard level FET

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